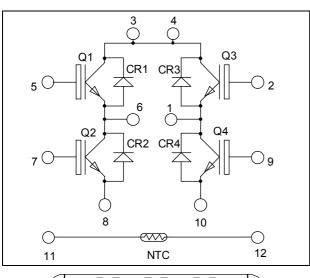
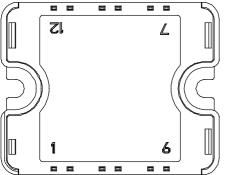


Full - Bridge Trench + Field Stop IGBT3

Power Module





Pins 3/4 must be shorted together

$V_{CES} = 600V$ $I_{C} = 75A^{*}$ @ Tc = 80°C

APTGT75H60T1G

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

| Symbol | Parameter | | Max ratings | Unit |
|------------------|---|----------------------------------|-------------|------|
| V _{CES} | Collector - Emitter Breakdown Voltage | | 600 | V |
| т | Continuous Collector Current | $T_C = 25^{\circ}C$ | 100* | |
| 1 _C | I _C Continuous Collector Current T | $T_C = 80^{\circ}C$ | 75* | А |
| I _{CM} | Pulsed Collector Current | $T_C = 25^{\circ}C$ | 140 | |
| V _{GE} | Gate – Emitter Voltage | | ±20 | V |
| PD | Maximum Power Dissipation | $T_C = 25^{\circ}C$ | 250 | W |
| RBSOA | Reverse Bias Safe Operating Area | $T_{\rm J} = 150^{\circ}{\rm C}$ | 150A @ 550V | |

* Specification of IGBT device but output current must be limited to 40A to not exceed a delta of temperature greater than 35°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified • • • •

| Electrical Characteristics | | | | | | | | | |
|----------------------------|--------------------------------------|--|-----|-----|-----|------|--|--|--|
| Symbol | Characteristic | Test Conditions | Min | Тур | Max | Unit | | | |
| I _{CES} | Zero Gate Voltage Collector Current | $V_{GE} = 0V, V_{CE} = 600V$ | | | 250 | μA | | | |
| V _{CE(sat)} | Collector Emitter Saturation Voltage | $V_{GE} = 15V$ $T_j = 25^{\circ}C$ | | 1.5 | 1.9 | V | | | |
| V CE(sat) | Concetor Emitter Saturation Voltage | $I_{\rm C} = 75 {\rm A}$ $T_{\rm j} = 150^{\circ} {\rm C}$ | 2 | 1.7 | | v | | | |
| V _{GE(th)} | Gate Threshold Voltage | $V_{GE} = V_{CE}, I_C = 600 \mu A$ | 5.0 | 5.8 | 6.5 | V | | | |
| I _{GES} | Gate – Emitter Leakage Current | $V_{GE} = 20V, V_{CE} = 0V$ | | | 600 | nA | | | |

Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min | Тур | Max | Unit | | |
|---------------------|------------------------------|---|------------------------|-----|------|------|------|--|
| Cies | Input Capacitance | $V_{GE} = 0V$ | | | 4620 | | | |
| C _{oes} | Output Capacitance | $V_{CE} = 25V$ | | | 300 | | pF | |
| C _{res} | Reverse Transfer Capacitance | f = 1 MHz | | 140 | | | | |
| T _{d(on)} | Turn-on Delay Time | Inductive Switching (25°C) | | | 110 | | | |
| Tr | Rise Time | $V_{GE} = \pm 15V$ | | | 45 | | ns | |
| T _{d(off)} | Turn-off Delay Time | $V_{Bus} = 300V$ $I_C = 75A$ | | | 200 | | | |
| T _f | Fall Time | $R_G = 4.7\Omega$ | | 40 | | | | |
| T _{d(on)} | Turn-on Delay Time | Inductive Switch $V_{GE} = \pm 15V$ | ning (150°C) | | 120 | | | |
| Tr | Rise Time | $V_{GE} = \pm 15 V$ $V_{Bus} = 300 V$ | | | 50 | | ns | |
| T _{d(off)} | Turn-off Delay Time | $I_{C} = 75A$ $R_{G} = 4.7\Omega$ | | | | 250 | | |
| T _f | Fall Time | | | | 60 | | | |
| Б | Turn on Switching Energy | $V_{GE} = \pm 15V$ | $T_j = 25^{\circ}C$ | | 0.35 | | mJ | |
| Eon | Turn-on Switching Energy | $V_{Bus} = 300V$ | $T_{j} = 150^{\circ}C$ | | 0.6 | | 111J | |
| Б | Turn-off Switching Energy | $I_{\rm C} = 75 \text{A}$ | $T_j = 25^{\circ}C$ | | 2.2 | | mJ | |
| E _{off} | run-on Switching Energy | $R_G = 4.7\Omega \qquad T_j = 150^{\circ}C$ | | 2.6 | | 111J | | |

Reverse diode ratings and characteristics

| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit |
|------------------|---|---------------------------------------|------------------------|------------------------|------|-----|------|
| V _{RRM} | Maximum Peak Repetitive Reverse Voltage | | | 600 | | | V |
| I _{RM} | Maximum Reverse Leakage Current | $V_{R}=600V$ | $T_j = 25^{\circ}C$ | | | 250 | μA |
| IRM | Maximum Reverse Leakage Current | VR 000V | $T_{j} = 150^{\circ}C$ | | | 500 | μΑ |
| I _F | DC Forward current | | $Tc = 80^{\circ}C$ | | 75 | | А |
| V _F | Diode Forward Voltage | $I_{\rm F} = 75 A$ $V_{\rm GE} = 0 V$ | $T_i = 25^{\circ}C$ | | 1.6 | 2 | |
| • F | blode i of ward voltage | | $T_i = 150^{\circ}C$ | | 1.5 | | V |
| t _{rr} | Reverse Recovery Time | | $T_j = 25^{\circ}C$ | | 100 | | ns |
| ۹r | Reverse receivery Time | | $T_{j} = 150^{\circ}C$ | | 150 | | 115 |
| Q _{rr} | Reverse Recovery Charge | | $T_j = 25^{\circ}C$ | | 3.6 | | |
| Qrr | Reverse Recovery Charge | | | $T_{j} = 150^{\circ}C$ | | 7.6 | |
| Er | Reverse Recovery Energy | | $T_i = 25^{\circ}C$ | | 0.85 | | mJ |
| Ľr | Reverse Recovery Energy | | $T_{j} = 150^{\circ}C$ | | 1.8 | | 1113 |

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Thermal and package characteristics

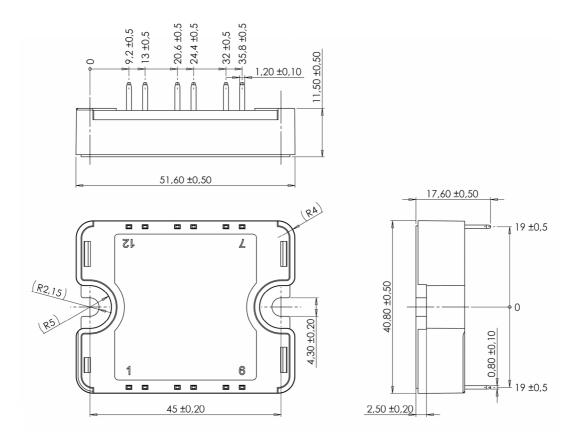
| Symbol | Characteristic | | | Min | Тур | Max | Unit |
|--------------------------|---|-------------|------|------|------|------|------|
| R _{thJC} | Junction to Case Thermal Resistance | IGBT | | | 0.60 | °C/W | |
| R _{thJC} | | Diode | | | 0.98 | C/ W | |
| V _{ISOL} | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz | | | 4000 | | | V |
| T _J | Operating junction temperature range | | | -40 | | 175 | |
| T _{STG} | Storage Temperature Range | | | -40 | | 125 | °C |
| T _C | Operating Case Temperature | | -40 | | 100 | | |
| Torque | Mounting torque | To heatsink | x M4 | 2 | | 3 | N.m |
| Wt | Package Weight | | | | | 80 | g |

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol | Characteristic | Min | Тур | Max | Unit |
|-----------------|-----------------------------|-----|------|-----|------|
| R ₂₅ | Resistance @ 25°C | | 50 | | kΩ |
| B 25/85 | $T_{25} = 298.15 \text{ K}$ | | 3952 | | K |

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

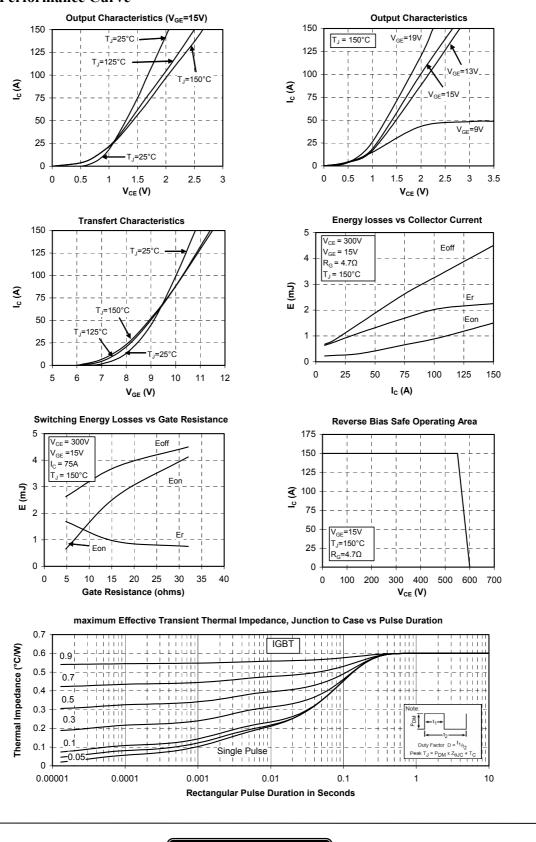
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Typical Performance Curve

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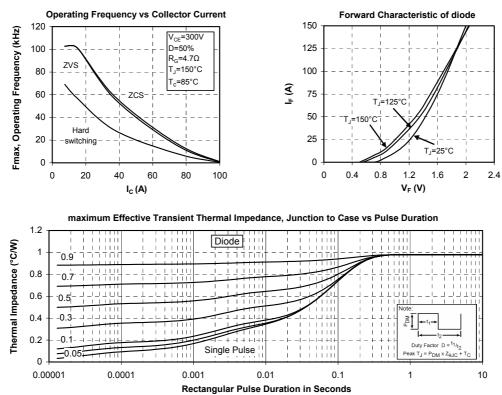
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